

FIG. 1 (CONVENTIONAL ART)

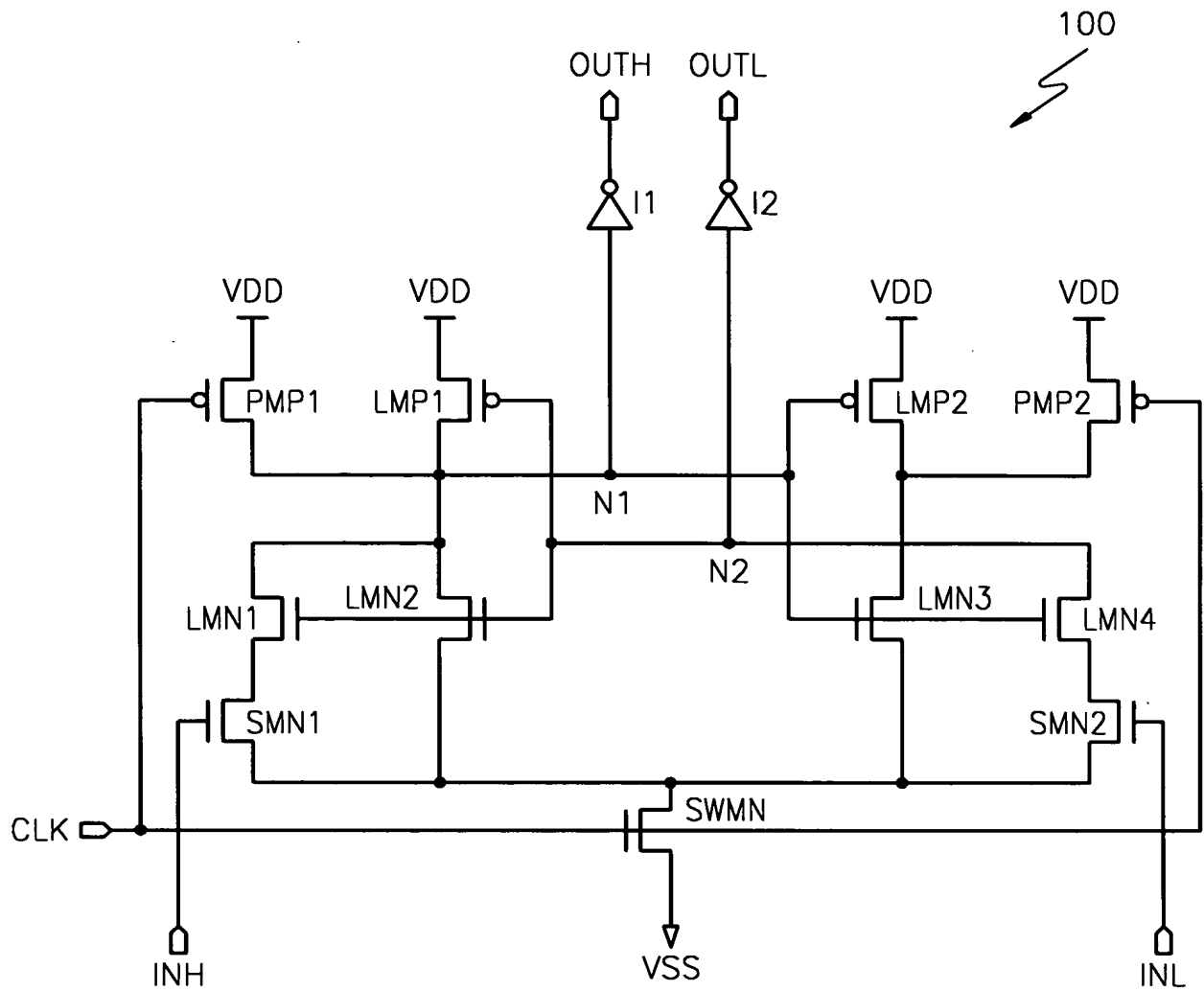


FIG. 2 (CONVENTIONAL ART)

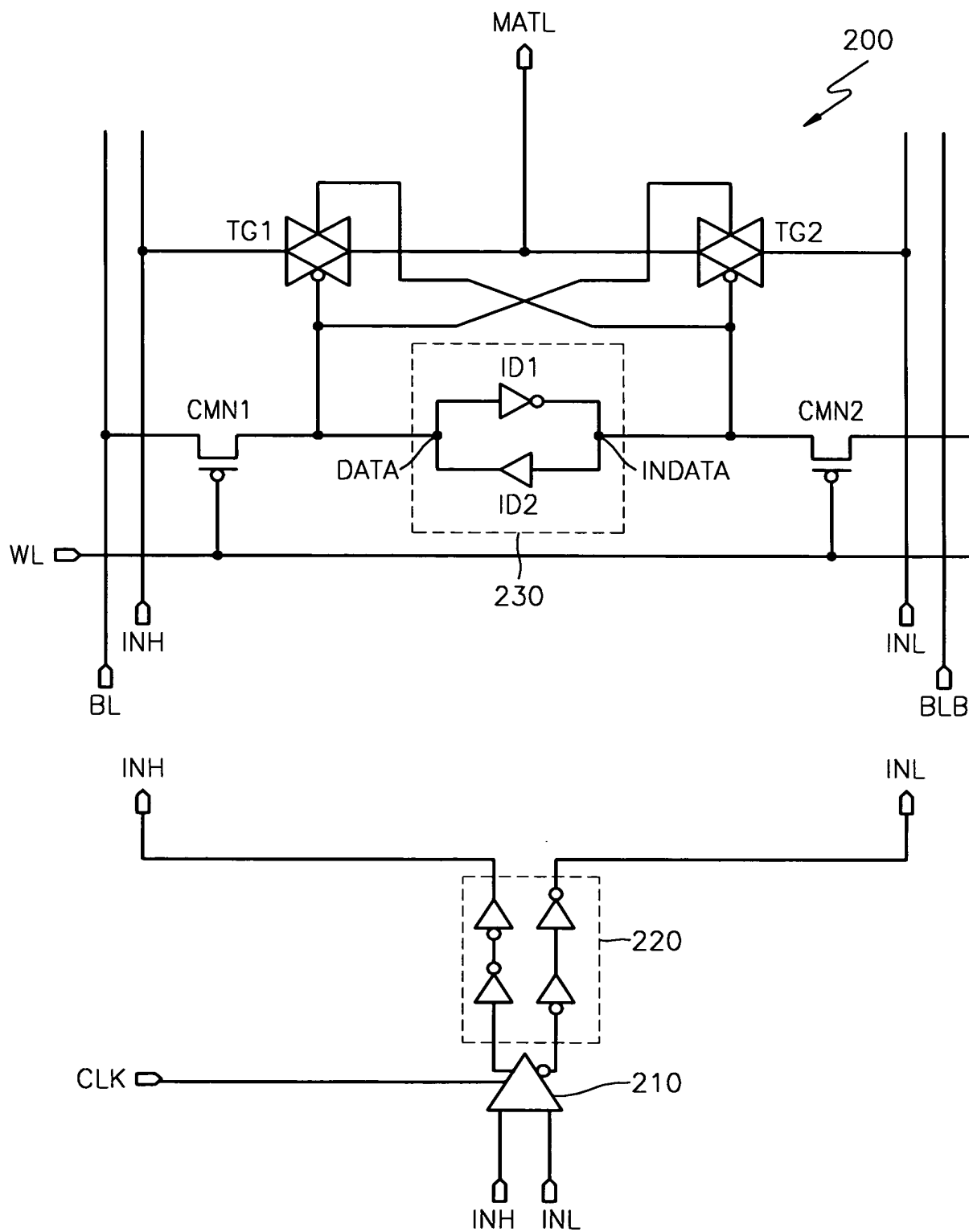


FIG. 3

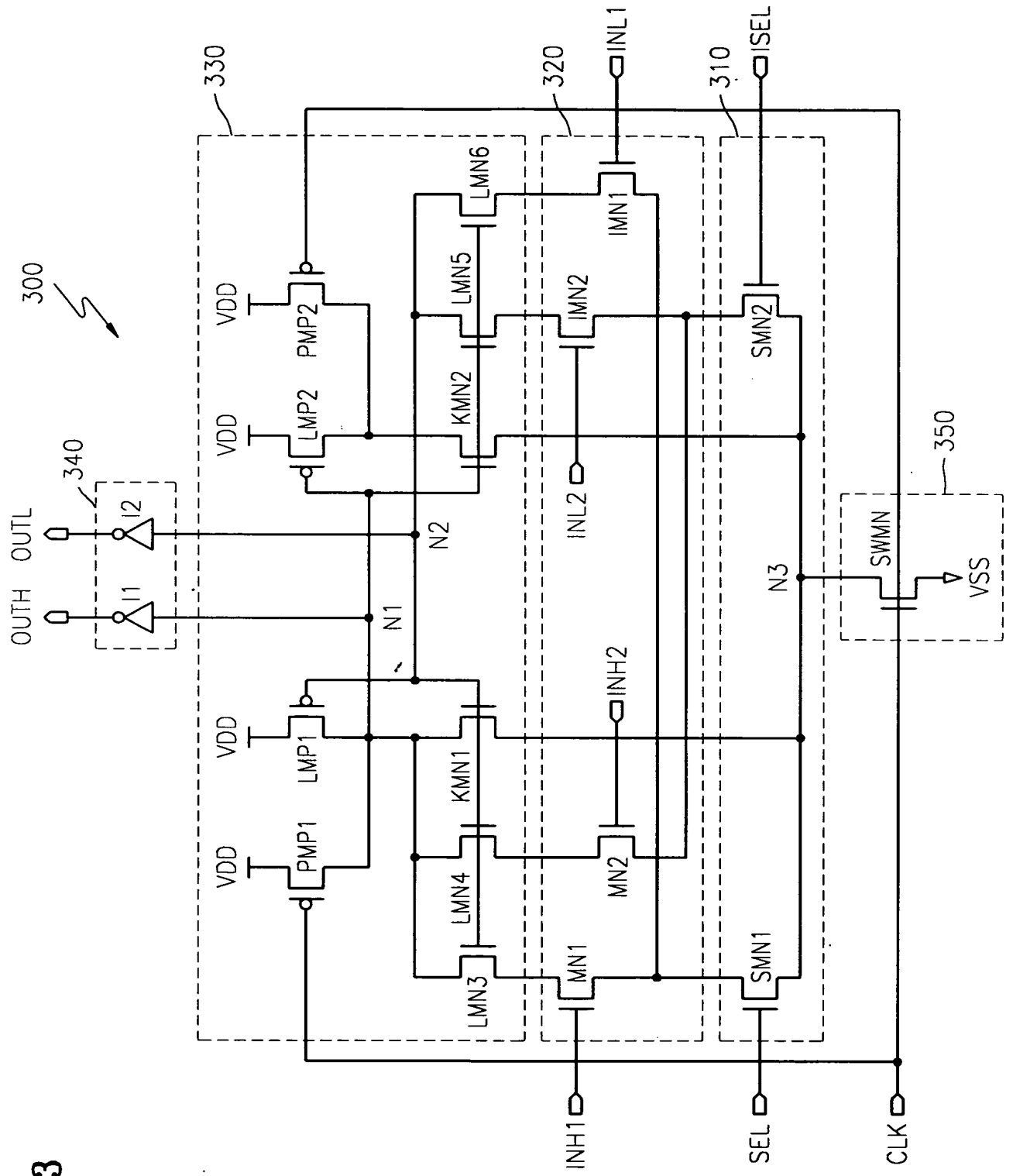


FIG. 4

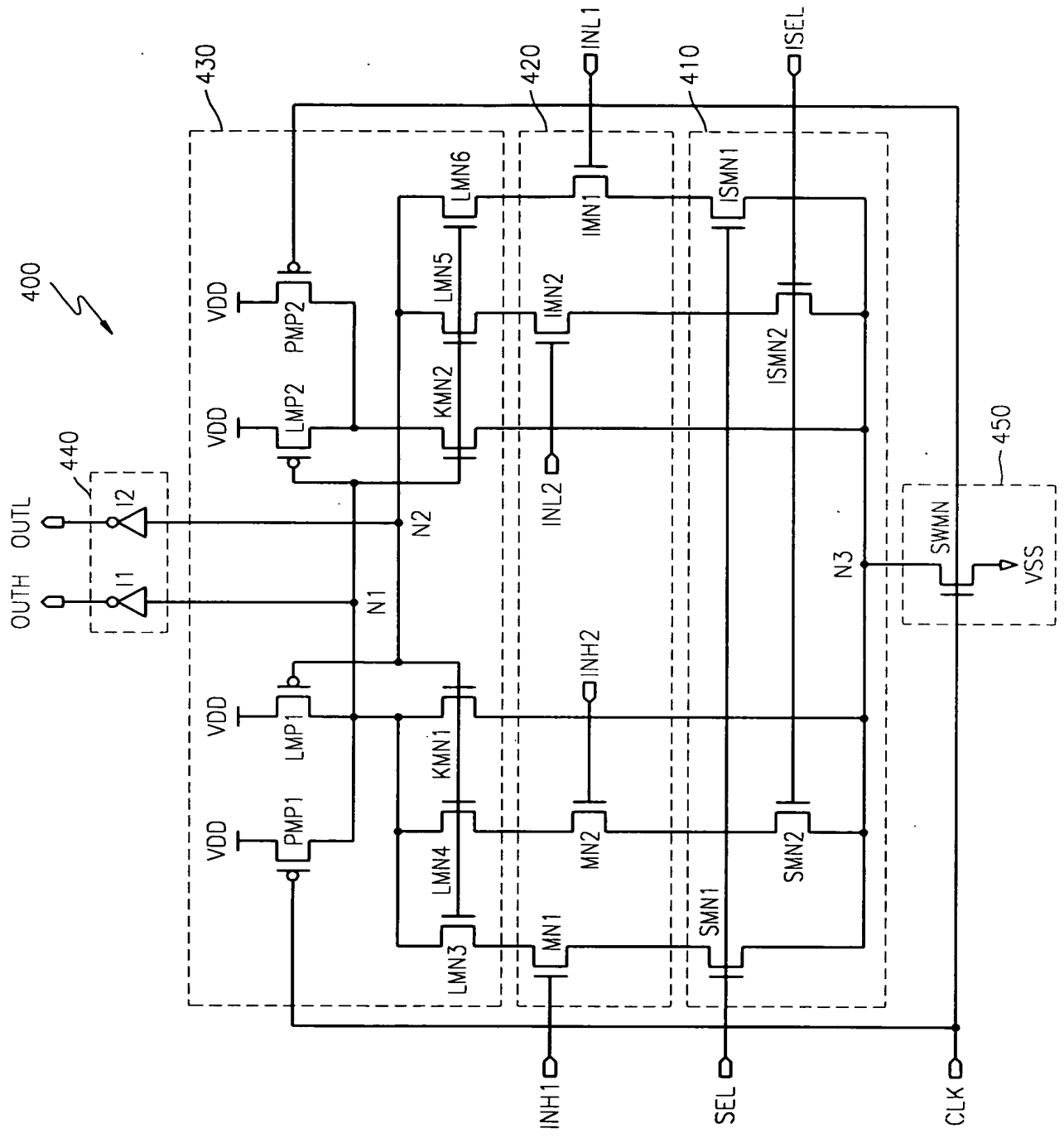


FIG. 5

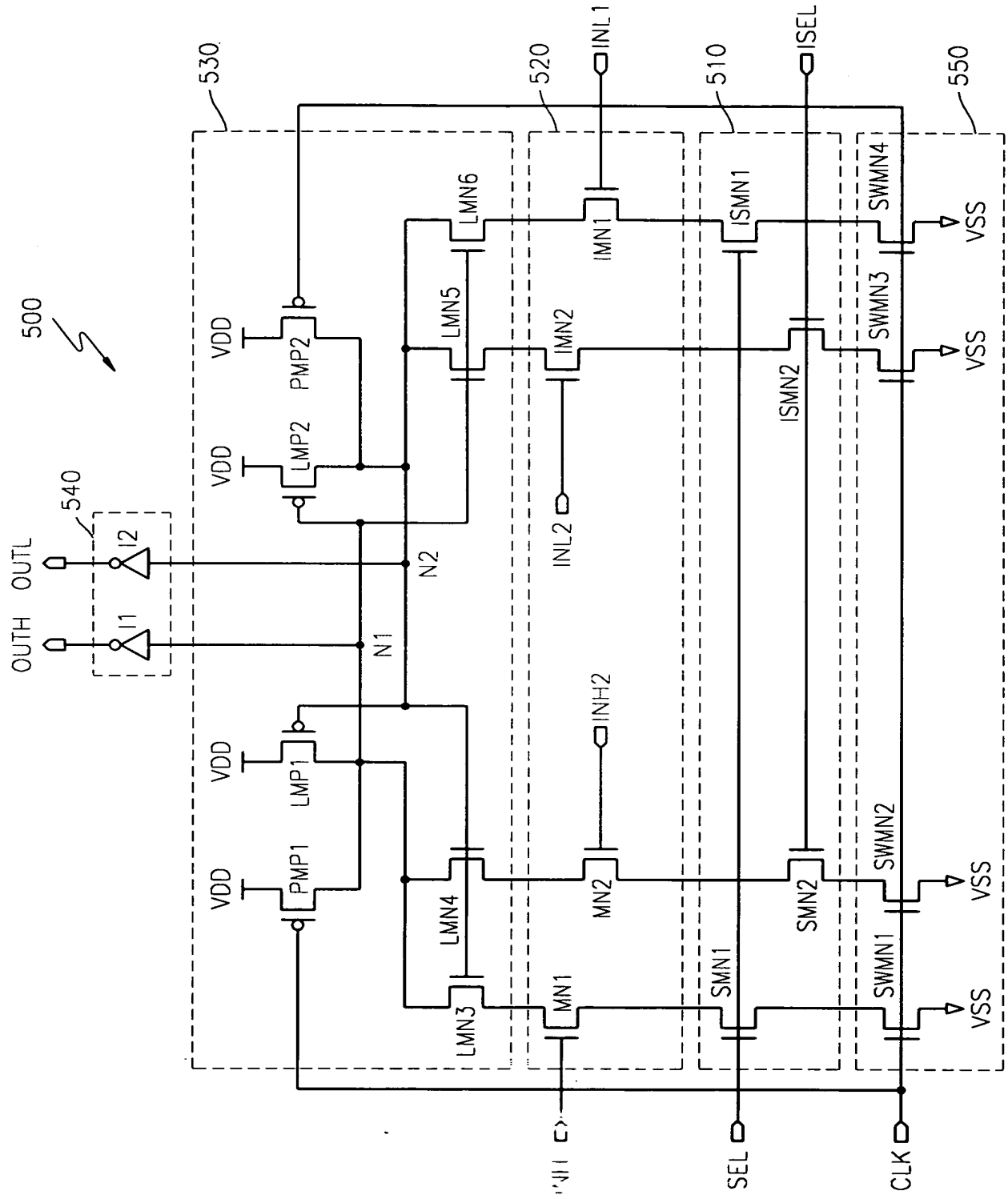
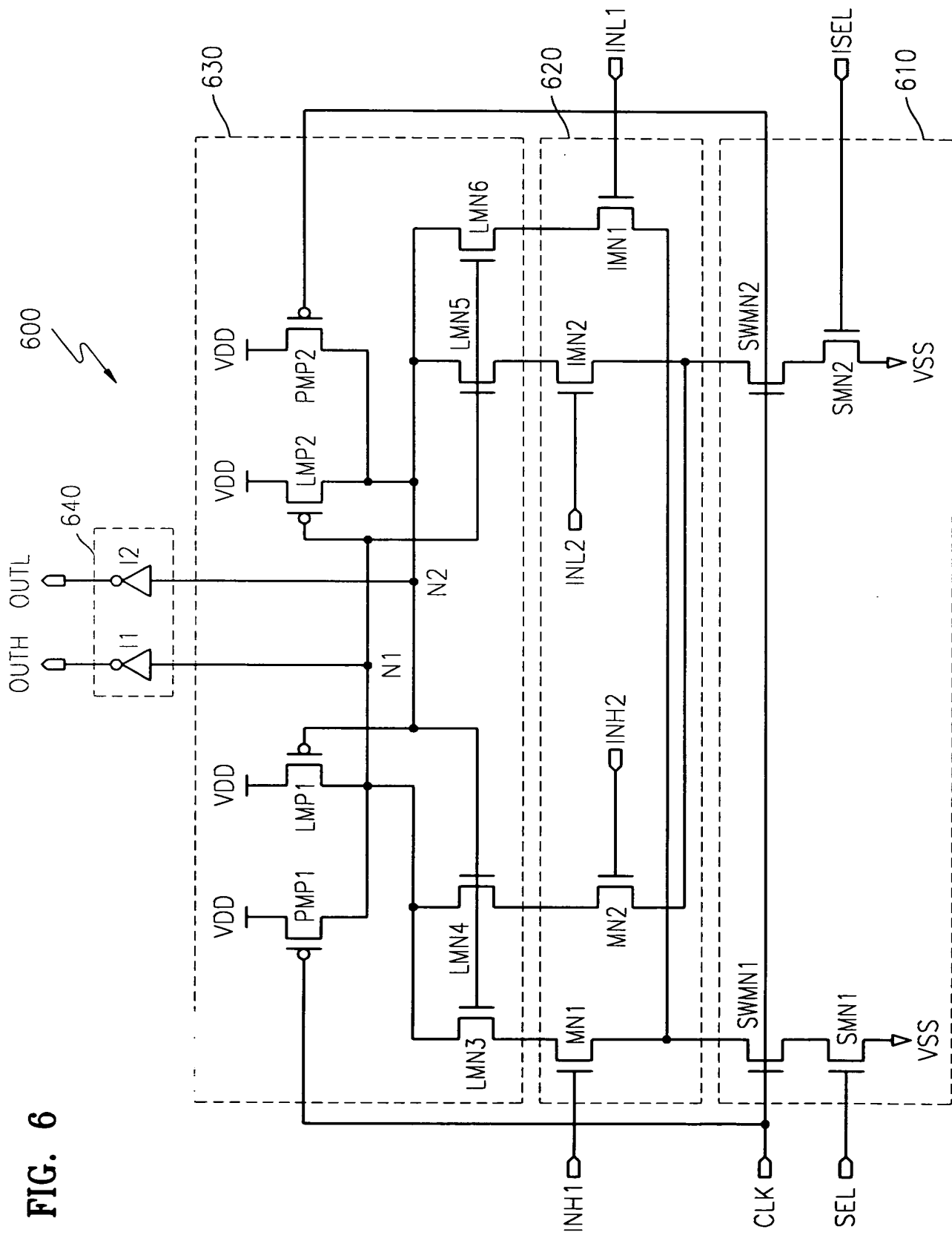
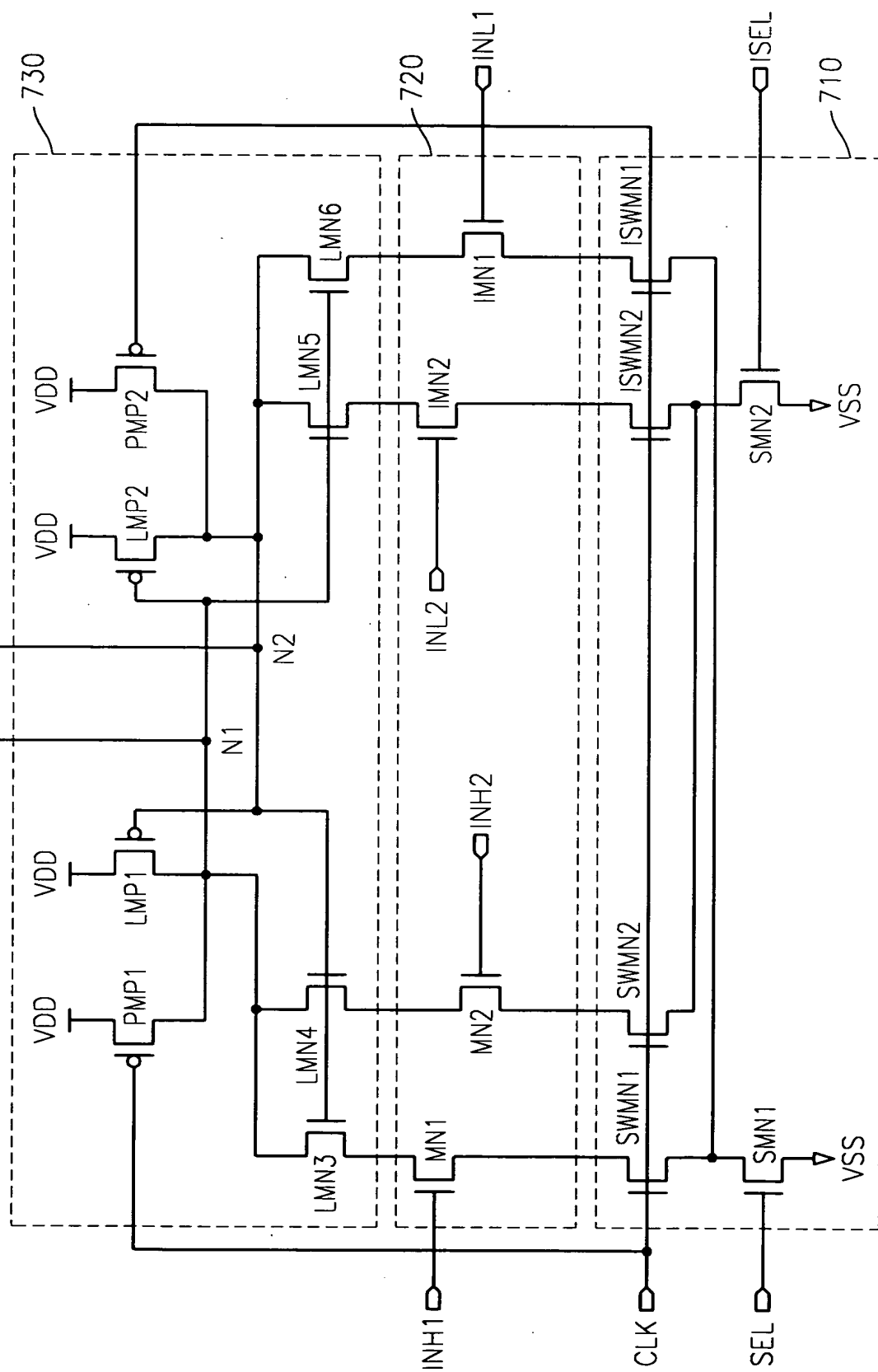
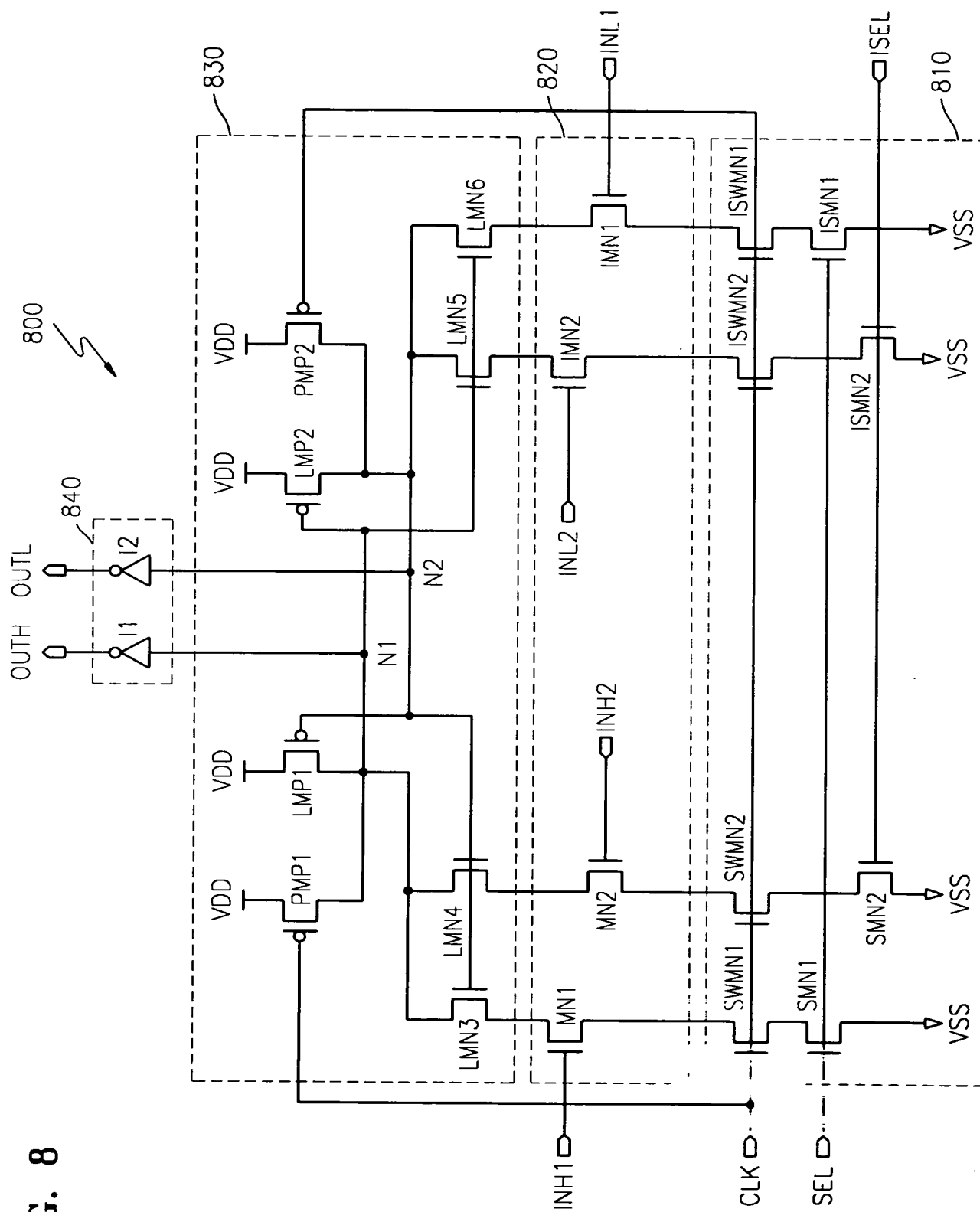


FIG. 6



[illegible]

003



The circuit diagram illustrates a 1T1R1C1 memory cell. It features a word line (WL) and a bit line (BL) intersecting at a storage node. The storage node is connected to a storage capacitor (C1) and a storage transistor (SMN1). The storage transistor (SMN1) is controlled by a word line select signal (SEL) and a word line inhibit signal (INH1). The storage node is also connected to a data line (DATA) through a data access transistor (ID1). The data access transistor (ID1) is controlled by a data line select signal (SEL) and a data line inhibit signal (INH2). The data line (DATA) is connected to a data line capacitor (C2) and a data line access transistor (ID2). The data line access transistor (ID2) is controlled by a data line select signal (SEL) and a data line inhibit signal (INH2). The data line (DATA) is also connected to a data line output transistor (ID2) which drives the data line output (OUTL). The data line output (OUTL) is connected to a data line output capacitor (C2) and a data line output transistor (ID2). The data line output (OUTL) is also connected to a data line output capacitor (C2) and a data line output transistor (ID2). The data line output (OUTL) is also connected to a data line output capacitor (C2) and a data line output transistor (ID2).

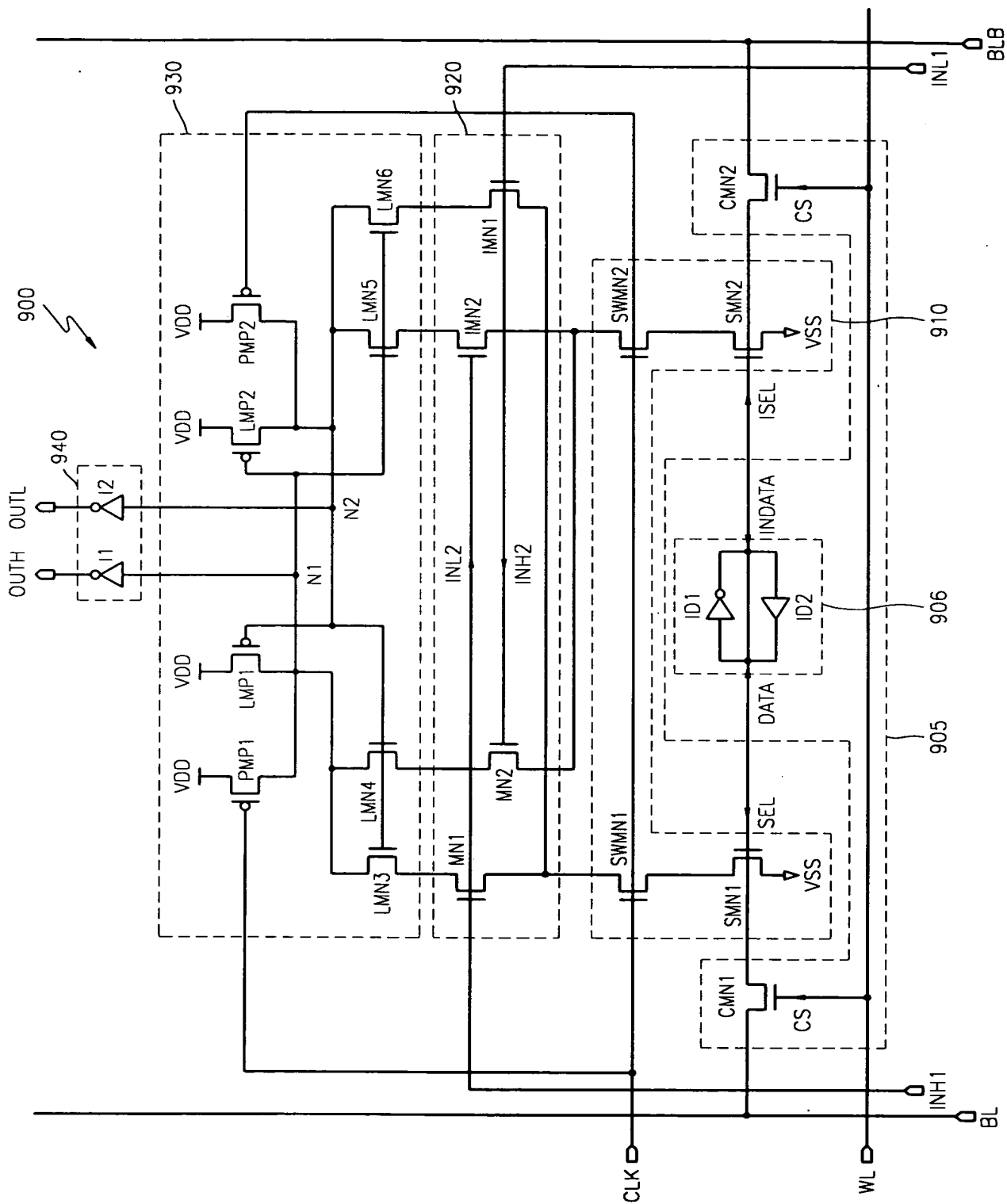


FIG. 10

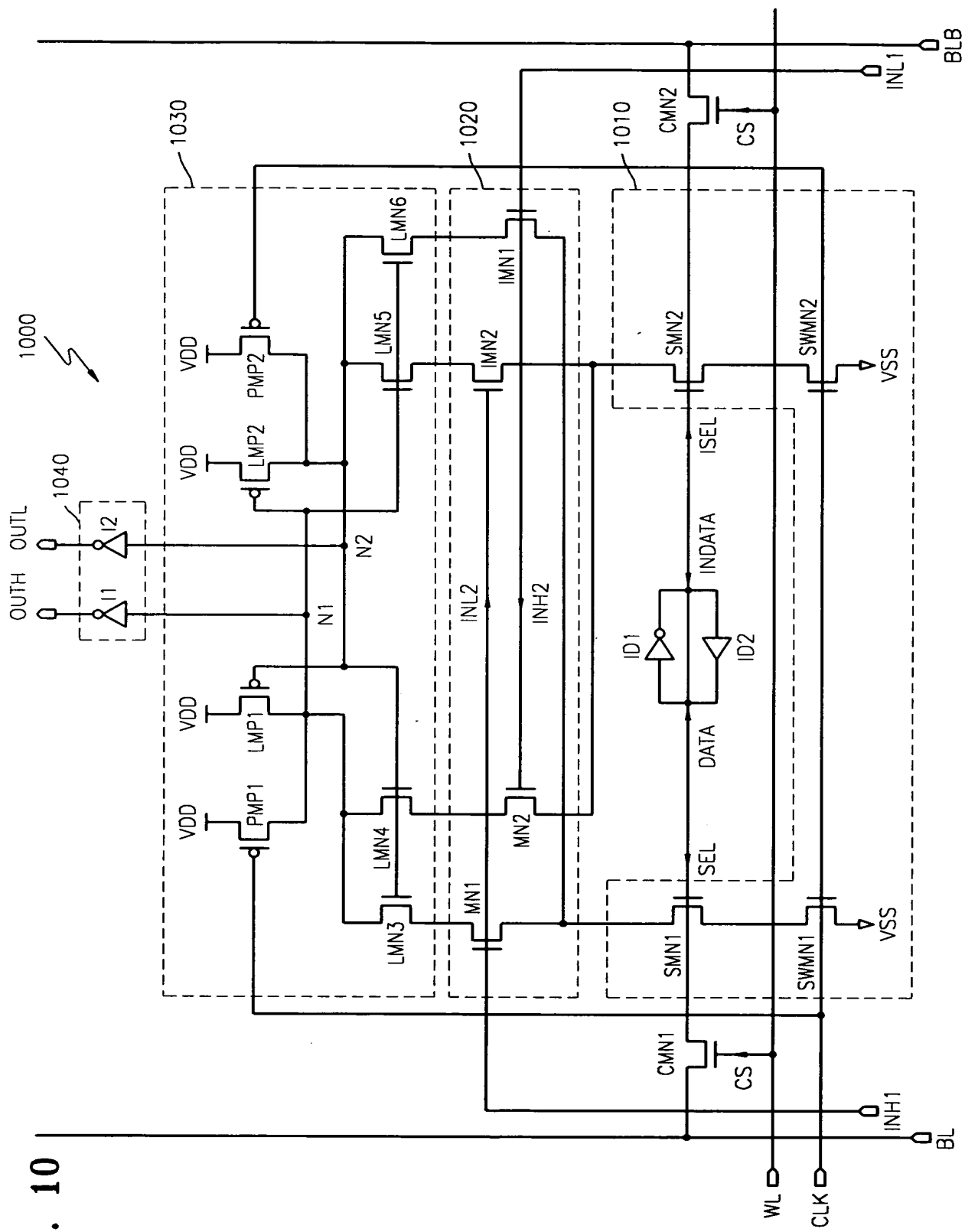


FIG. 11

